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(54) Title: HIGH MODULUS CARBON DOPED SILICON OXIDE FILM FOR MOLD STACK SCALING SOLUTIONS IN AD-
VANCED MEMORY APPLICATIONS

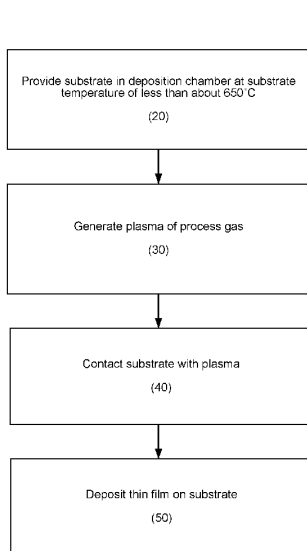


FIG. 1

(57) Abstract: Provided are reduced temperature plasma enhanced chemical vapor de-
position processes for producing high modulus oxide thin films on a substrate. The sub-
strate temperature for deposition of the oxide thin film is less than about 700°C.

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